

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07363 07-33-23

SILICON PNP TRIPLE DIFFUSED TYPE

2SB863

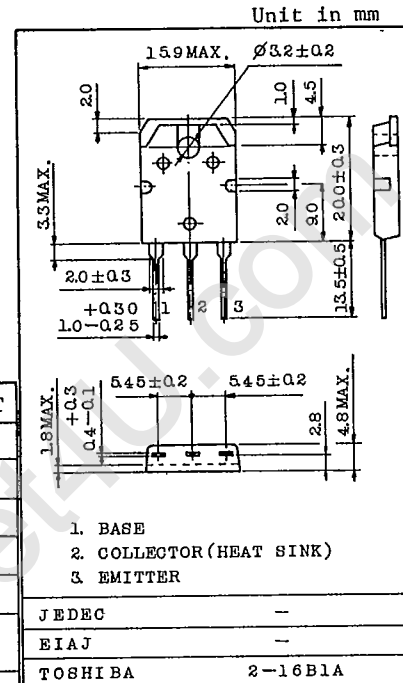
o POWER AMPLIFIER APPLICATIONS.

FEATURES:

- Complementary to 2SD1148
- Recommend for 70W High Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	VCBO	-140	V
Collector-Emitter Voltage	VCEO	-140	V
Emitter-Base Voltage	VEBO	-5	V
Collector Current	IC	-10	A
Base Current	IB	-1	A
Collector Power Dissipation (Tc=25°C)	PC	100	W
Junction Temperature	Tj	150	°C
Storage Temperature Range	Tstg	-55~150	°C



Weight : 4.6g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	VCB=-140V, IE=0	-	-	-5.0	μA
Emitter Cut-off Current	IEBO	VEB=-5V, IC=0	-	-	-5.0	μA
Collector-Emitter Breakdown Voltage	V(BR)CEO	IC=-50mA, IB=0	-140	-	-	V
DC Current Gain	hFE(1) (Note)	VCE=-5V, IC=-1A	55	-	160	
	hFE(2)	VCE=-5V, IC=-5A	25	-	-	
Collector-Emitter Saturation Voltage	VCE(sat)	IC=-5A, IB=-0.5A	-	-0.6	-2.0	V
Base-Emitter Voltage	VBE	VCE=-5V, IC=-5A	-	-0.96	-1.5	V
Transition Frequency	fT	VCE=-10V, IC=-1A	-	15	-	MHz
Collector Output Capacitance	Cob	VCB=-10V, IE=0, f=1MHz	-	400	-	pF

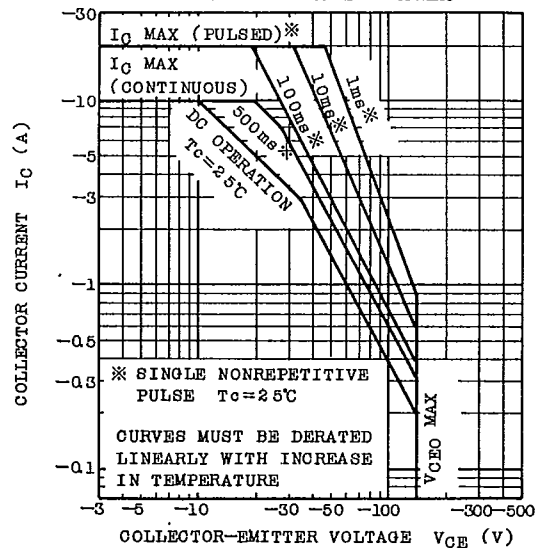
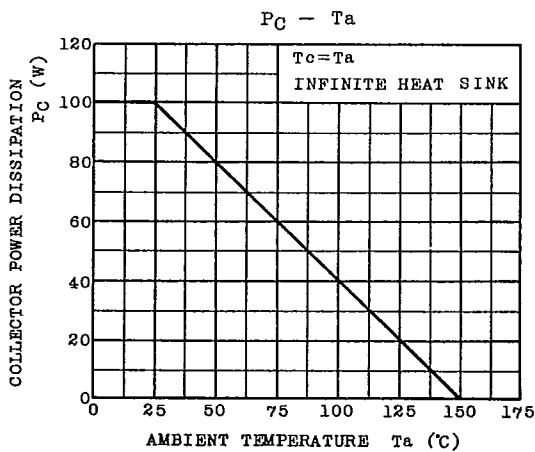
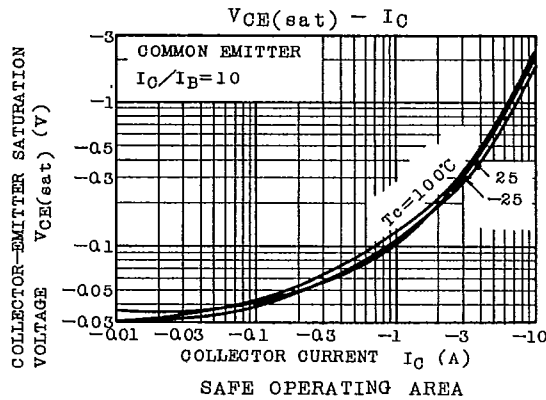
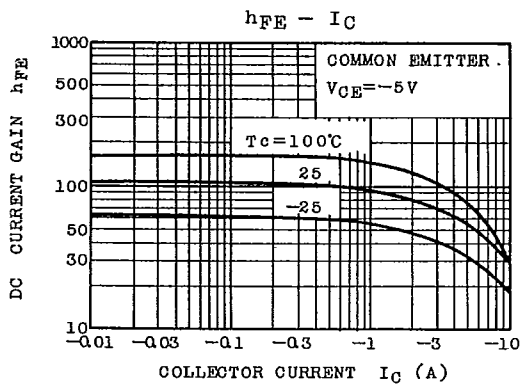
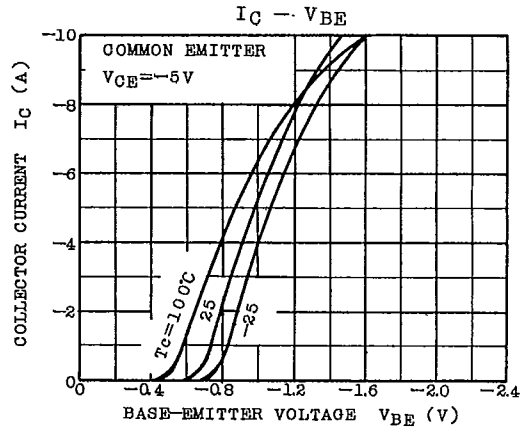
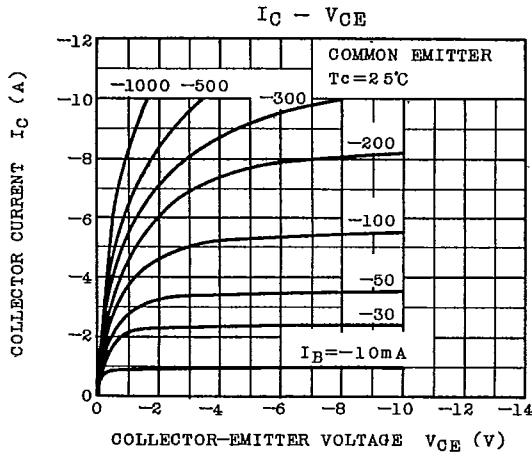
Note: hFE(1) Classification R : 55~110 O : 80~160

TOSHIBA CORPORATION

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